Silicon PNP Power Transistors BD240/A/B/C

DESCRIPTION

・With TO-220C package
・Complement to type BD239/A/B/C

APPLICATIONS

・For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

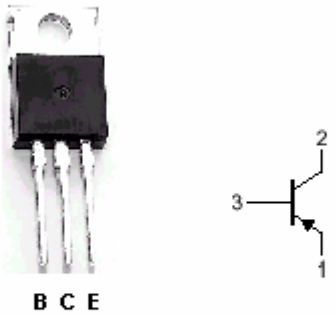


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BD240	Open emitter	-55	V
		BD240A		-70	
		BD240B		-90	
		BD240C		-115	
V_{CEO}	Collector-emitter voltage	BD240	Open base	-45	V
		BD240A		-60	
		BD240B		-80	
		BD240C		-100	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-2	A
I_{CM}	Collector current-peak			-4	A
I_B	Base current			-0.6	A
P_C	Collector power dissipation		T_C=25℃	30	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-65~150	℃

固电半导体 INCHANGE SEMICONDUCTOR

Silicon PNP Power Transistors BD240/A/B/C

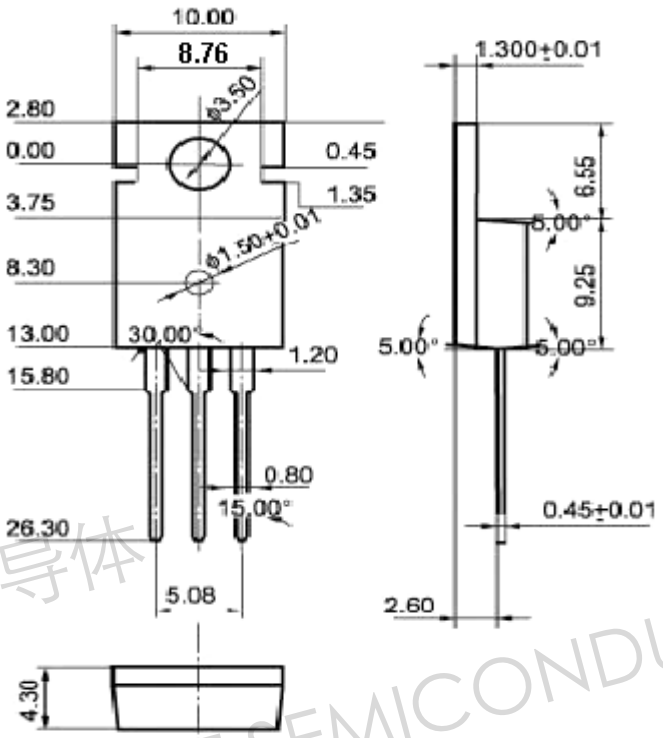
CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	BD240	I_C=-30mA; I_B=0	-45			V
		BD240A		-60			
		BD240B		-80			
		BD240C		-100			
V_{CEsat}	Collector-emitter saturation voltage		I_C=-1 A;I_B=-0.2 A			-0.7	V
V_{BE}	Base-emitter on voltage		I_C=-1A ; V_{CE}=-4V			-1.3	V
I_{CEO}	Collector cut-off current	BD240/A	V_{CE}=-30V; I_B=0			-0.3	mA
		BD240B/C	V_{CE}=-60V; I_B=0				
I_{CES}	Collector cut-off current	BD240	V_{CE}=-45V; V_{BE}=0			-0.2	mA
		BD240A	V_{CE}=-60V; V_{BE}=0				
		BD240B	V_{CE}=-80V; V_{BE}=0				
		BD240C	V_{CE}=-100V; V_{BE}=0				
I_{EBO}	Emitter cut-off current		V_{EB}=-5V; I_C=0			-1	mA
h_{FE-1}	DC current gain		I_C=-0.2A ; V_{CE}=-4V	40			
h_{FE-2}	DC current gain		I_C=-1A ; V_{CE}=-4V	15			

固电半导体 INCHANGE SEMICONDUCTOR

PACKAGE OUTLINE



固电半导体
INCHANGE SEMICONDUCTOR

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)